

Erratum to: Design and theoretical comparison of input ESD devices in 180 nm CMOS with focus on low capacitance

A. Michalowska-Forsyth, P. Schrey, B. Deutschmann

Published online October 9, 2018
© Springer-Verlag GmbH Austria, ein Teil von Springer Nature 2018



Erratum to: Elektrotechnik & Informationstechnik (2018)
135/1: 69–75
<https://doi.org/10.1007/s00502-017-0569-0>

Following **Acknowledgement** was missing:

The financial support of the presented research work by the Austrian Science Fund (FWF) under the project number T 756-N20 is gratefully acknowledged.

The online version of the original article can be found under
<https://doi.org/10.1007/s00502-017-0569-0>.

Michalowska-Forsyth, Alicja, Graz University of Technology, Institute of Electronics, Inffeldgasse 12/I, Graz 8010, Austria (E-mail: alicja.michalowska@tugraz.at); **Schrey, Patrick**, Graz University of Technology, Institute of Electronics, Inffeldgasse 12/I, Graz 8010, Austria; **Deutschmann, Bernd**, Graz University of Technology, Institute of Electronics, Inffeldgasse 12/I, Graz 8010, Austria